

## **Semiconductor Devices Physics Technology 2nd Edition**

An in-depth, up-to-date presentation of the physics and operational principles of all modern semiconductor devices. The companion volume to Dr. Sze's classic *Physics of Semiconductor Devices*, *Modern Semiconductor Device Physics* covers all the significant advances in the field over the past decade. To provide the most authoritative, state-of-the-art information on this rapidly developing technology, Dr. Sze has gathered the contributions of world-renowned experts in each area. Principal topics include bipolar transistors, compound-semiconductor field-effect-transistors, MOSFET and related devices, power devices, quantum-effect and hot-electron devices, active microwave diodes, high-speed photonic devices, and solar cells. Supported by hundreds of illustrations and references and a problem set at the end of each chapter, *Modern Semiconductor Device Physics* is the essential text/reference for electrical engineers, physicists, material scientists, and graduate students actively working in microelectronics and related fields.

*Laser Annealing Processes in Semiconductor Technology: Theory, Modeling and Applications in Nanoelectronics* synthesizes the scientific and technological advances of laser annealing processes for current and emerging nanotechnologies. The book provides an overview of the laser-matter interactions of materials and recent advances in modeling of laser-related phenomena, with the bulk of the book focusing on current and emerging (beyond-CMOS) applications. Reviewed applications include laser annealing of CMOS, group IV semiconductors, superconducting materials, photonic materials, 2D materials. This comprehensive book is ideal for post-graduate students, new entrants, and experienced

researchers in academia, research and development in materials science, physics and engineering. Introduces the fundamentals of laser materials and device fabrication methods, including laser-matter interactions and laser-related phenomena Addresses advances in physical modeling and in predictive simulations of laser annealing processes such as atomistic modeling and TCAD simulations Reviews current and emerging applications of laser annealing processes such as CMOS technology and group IV semiconductors

This book demonstrates the role and abilities of fluctuation in semiconductor physics, and shows what kinds of physical information are involved in the noise characteristics of semiconductor materials and devices, how this information may be decoded and which advantages are inherent to the noise methods. The text provides a comprehensive account of current results, addressing problems which have not previously been covered in Western literature, including the excess noise of tunnel-recombination currents and photocurrents in diodes, fluctuation phenomena in a real photoconductor with different recombination centers, and methods of noise spectroscopy of levels in a wide range of materials and devices.

Devices based on disordered semiconductors have wide applications. It is difficult to imagine modern life without printers and copiers, LCD monitors and TVs, optical disks, economical solar cells, and many other devices based on disordered semiconductors. However, nowadays books that discuss disordered (amorphous, nanocrystalline, microcrystalline)

Nonequilibrium hot charge carriers play a crucial role in the physics and technology of semiconductor nanostructure devices. This book, one of the first on the topic, discusses fundamental aspects of hot carriers in quasi-two-dimensional systems and the impact of these carriers on semiconductor devices. The work will provide scientists and device engineers with

an authoritative review of the most exciting recent developments in this rapidly moving field. It should be read by all those who wish to learn the fundamentals of contemporary ultra-small, ultra-fast semiconductor devices. Topics covered include Reduced dimensionality and quantum wells Carrier-phonon interactions and hot phonons Femtosecond optical studies of hot carrier Ballistic transport Submicron and resonant tunneling devices

The new edition of the most detailed and comprehensive single-volume reference on major semiconductor devices The Fourth Edition of Physics of Semiconductor Devices remains the standard reference work on the fundamental physics and operational characteristics of all major bipolar, unipolar, special microwave, and optoelectronic devices. This fully updated and expanded edition includes approximately 1,000 references to original research papers and review articles, more than 650 high-quality technical illustrations, and over two dozen tables of material parameters. Divided into five parts, the text first provides a summary of semiconductor properties, covering energy band, carrier concentration, and transport properties. The second part surveys the basic building blocks of semiconductor devices, including p-n junctions, metal-semiconductor contacts, and metal-insulator-semiconductor (MIS) capacitors. Part III examines bipolar transistors, MOSFETs (MOS field-effect transistors), and other field-effect transistors such as JFETs (junction field-effect-transistors) and MESFETs (metal-semiconductor field-effect transistors). Part IV focuses on negative-resistance and power devices. The book concludes with coverage of photonic devices and sensors, including light-emitting diodes (LEDs), solar cells, and various photodetectors and semiconductor sensors. This classic volume, the standard textbook and reference in the field of semiconductor devices: Provides the practical foundation necessary for understanding the devices currently in use and

evaluating the performance and limitations of future devices Offers completely updated and revised information that reflects advances in device concepts, performance, and application Features discussions of topics of contemporary interest, such as applications of photonic devices that convert optical energy to electric energy Includes numerous problem sets, real-world examples, tables, figures, and illustrations; several useful appendices; and a detailed solutions manual Explores new work on leading-edge technologies such as MODFETs, resonant-tunneling diodes, quantum-cascade lasers, single-electron transistors, real-space-transfer devices, and MOS-controlled thyristors Physics of Semiconductor Devices, Fourth Edition is an indispensable resource for design engineers, research scientists, industrial and electronics engineering managers, and graduate students in the field.

Introduction to Semiconductor Device Physics is a popular and established text that offers a thorough introduction to the underlying physics of semiconductor devices. It begins with a review of basic solid state physics, then goes on to describe the properties of semiconductors including energy bands, the concept of effective mass, carrier concentration, and conduction in more detail. Thereafter the book is concerned with the principles of operation of specific devices, beginning with the Gunn Diode and the p-n junction. The remaining chapters cover the on specific devices, including the LED, the bipolar transistor, the field-effect transistor, and the semiconductor laser. The book concludes with a chapter providing a brief introduction to quantum theory. Not overtly mathematical, Introduction to Semiconductor Device Physics introduces only those physical concepts required for an understanding of the semiconductor devices being considered. The author's intuitive style, coupled with an extensive set of worked problems, make this the ideal introductory text for those concerned with understanding

electrical and electronic engineering, applied physics, and related subjects.

This book disseminates the current knowledge of semiconductor physics and its applications across the scientific community. It is based on a biennial workshop that provides the participating research groups with a stimulating platform for interaction and collaboration with colleagues from the same scientific community. The book discusses the latest developments in the field of III-nitrides; materials & devices, compound semiconductors, VLSI technology, optoelectronics, sensors, photovoltaics, crystal growth, epitaxy and characterization, graphene and other 2D materials and organic semiconductors.

This textbook provides a theoretical background for contemporary trends in solid-state theory and semiconductor device physics. It discusses advanced methods of quantum mechanics and field theory and is therefore primarily intended for graduate students in theoretical and experimental physics who have already studied electrodynamics, statistical physics, and quantum mechanics. It also relates solid-state physics fundamentals to semiconductor device applications and includes auxiliary results from mathematics and quantum mechanics, making the book useful also for graduate students in electrical engineering and material science. Key Features: Explores concepts common in textbooks on semiconductors, in addition to topics not included in similar books currently available on the market, such as the topology of Hilbert space in crystals Contains the latest research and developments in the field Written in an accessible yet rigorous manner

This text is a first attempt to pull together the whole of semiconductor science and

technology since 1970 in so far as semiconductor multilayers are concerned. Material, technology, physics and device issues are described with approximately equal emphasis, and form a single coherent point of view. The subject matter is the concern of over half of today's active semiconductor scientists and technologists, the remainder working on bulk semiconductors and devices. It is now routine to design and the prepare semiconductor multilayers at a time, with independent control over the dropping and composition in each layer. In turn these multilayers can be patterned with features that as a small as a few atomic layers in lateral extent. The resulting structures open up many new ares of exciting solid state and quantum physics. They have also led to whole new generations of electronic and optoelectronic devices whose superior performance relates back to the multilayer structures. The principles established in the field have several decades to go, advancing towards the ultimate of materials engineering, the design and preparation of solids atom by atom. The book should appeal equally to physicists, electronic engineers and materials scientists.

Market\_Desc: · Electrical Engineers· Scientists  
Special Features: · Provides strong coverage of all key semiconductor devices. Includes basic physics and material properties of key semiconductors· Covers all important processing technologies  
About The Book: This book is an introduction to the physical principles of modern semiconductor devices and their advanced fabrication technology. It begins with a brief historical review of major devices and key technologies and is then divided into three

sections: semiconductor material properties, physics of semiconductor devices and processing technology to fabricate these semiconductor devices.

This book deals mainly with physical device models which are developed from the carrier transport physics and device geometry considerations. The text concentrates on silicon and gallium arsenide devices and includes models of silicon bipolar junction transistors, junction field effect transistors (JFETs), MESFETs, silicon and GaAs MESFETs, transferred electron devices, pn junction diodes and Schottky varactor diodes. The modelling techniques of more recent devices such as the heterojunction bipolar transistors (HBT) and the high electron mobility transistors are discussed. This book contains details of models for both equilibrium and non-equilibrium transport conditions. The modelling Technique of Small-scale devices is discussed and techniques applicable to submicron-dimensioned devices are included. A section on modern quantum transport analysis techniques is included. Details of essential numerical schemes are given and a variety of device models are used to illustrate the application of these techniques in various fields.

The Third Edition of the standard textbook and reference in the field of semiconductor devices This classic book has set the standard for advanced study and reference in the semiconductor device field. Now completely updated and reorganized to reflect the tremendous advances in device concepts and performance, this Third Edition remains the most detailed and exhaustive single source of information on the most important

semiconductor devices. It gives readers immediate access to detailed descriptions of the underlying physics and performance characteristics of all major bipolar, field-effect, microwave, photonic, and sensor devices. Designed for graduate textbook adoptions and reference needs, this new edition includes: A complete update of the latest developments New devices such as three-dimensional MOSFETs, MODFETs, resonant-tunneling diodes, semiconductor sensors, quantum-cascade lasers, single-electron transistors, real-space transfer devices, and more Materials completely reorganized Problem sets at the end of each chapter All figures reproduced at the highest quality

Physics of Semiconductor Devices, Third Edition offers engineers, research scientists, faculty, and students a practical basis for understanding the most important devices in use today and for evaluating future device performance and limitations. A Solutions Manual is available from the editorial department.

Semiconductor Device Physics and Design teaches readers how to approach device design from the point of view of someone who wants to improve devices and can see the opportunity and challenges. It begins with coverage of basic physics concepts, including the physics behind polar heterostructures and strained heterostructures. The book then details the important devices ranging from p-n diodes to bipolar and field effect devices. By relating device design to device performance and then relating device needs to system use the student can see how device design works in the real world.

This book is an introduction to the physical principles of modern semiconductor devices and their advanced fabrication technology. It begins with a brief historical review of major devices and key technologies and is then divided into three sections: semiconductor material properties, physics of semiconductor devices and processing technology to fabricate these semiconductor devices.

The awaited revision of *Semiconductor Devices: Physics and Technology* offers more than 50% new or revised material that reflects a multitude of important discoveries and advances in device physics and integrated circuit processing. Offering a basic introduction to physical principles of modern semiconductor devices and their advanced fabrication technology, the third edition presents students with theoretical and practical aspects of every step in device characterizations and fabrication, with an emphasis on integrated circuits. Divided into three parts, this text covers the basic properties of semiconductor materials, emphasizing silicon and gallium arsenide; the physics and characteristics of semiconductor devices bipolar, unipolar special microwave and photonic devices; and the latest processing technologies, from crystal growth to lithographic pattern transfer.

*Physics of Semiconductor Devices* covers both basic classic topics such as energy band theory and the gradual-channel model of the MOSFET as well as advanced concepts and devices such as MOSFET short-channel effects, low-dimensional devices and single-electron transistors. Concepts are introduced to the reader in a simple way, often using comparisons to

everyday-life experiences such as simple fluid mechanics. They are then explained in depth and mathematical developments are fully described. Physics of Semiconductor Devices contains a list of problems that can be used as homework assignments or can be solved in class to exemplify the theory. Many of these problems make use of Matlab and are aimed at illustrating theoretical concepts in a graphical manner.

"This dynamic text applies physics concepts and equations to practical, real-world applications of semiconductor device theory"--

This book is a comprehensive text on the physics of semiconductors and nanostructures for a large spectrum of students at the final undergraduate level studying physics, material science and electronics engineering. It offers introductory and advanced courses on solid state and semiconductor physics on one hand and the physics of low dimensional semiconductor structures on the other in a single text book. Key Features Presents basic concepts of quantum theory, solid state physics, semiconductors, and quantum nanostructures such as quantum well, quantum wire, quantum dot and superlattice In depth description of semiconductor heterojunctions, lattice strain and modulation doping technique Covers transport in nanostructures under an electric and magnetic field with the topics: quantized conductance, Coulomb blockade, and integer and fractional quantum Hall effect Presents the optical processes in nanostructures under a magnetic field Includes illustrative problems with hints for solutions in each chapter Physics of Semiconductors and Nanostructures will be helpful to students initiating PhD work in the field of semiconductor nanostructures and devices. It follows a unique tutorial approach meeting the requirements of students who find learning the concepts difficult and want to study from a physical perspective.

"This well organized reference book covers the newest and most important practically applicable results in thin film-based semiconductor (A2B6-A4B6 and chalcogenide) sensors, heterojunction-based active elements and other devices. This book is written for "

This textbook describes the basic physics of semiconductors, including the hierarchy of transport models, and connects the theory with the functioning of actual semiconductor devices. Details are worked out carefully and derived from the basic physical concepts, while keeping the internal coherence of the analysis and explaining the different levels of approximation. Coverage includes the main steps used in the fabrication process of integrated circuits: diffusion, thermal oxidation, epitaxy, and ion implantation. Examples are based on silicon due to its industrial importance. Several chapters are included that provide the reader with the quantum-mechanical concepts necessary for understanding the transport properties of crystals. The behavior of crystals incorporating a position-dependent impurity distribution is described, and the different hierarchical transport models for semiconductor devices are derived (from the Boltzmann transport equation to the hydrodynamic and drift-diffusion models). The transport models are then applied to a detailed description of the main semiconductor-device architectures (bipolar, MOS, CMOS), including a number of solid-state sensors. The final chapters are devoted to the measuring methods for semiconductor-device parameters, and to a brief illustration of the scaling rules and numerical methods applied to the design of semiconductor devices.

"The textbook combines a thorough theoretical treatment of the basic physics of semiconductors with applications to practical devices by putting special emphasis on the physical principles upon which these devices operate. - "Graduate students and lecturers in

semiconductor physics, condensed matter physics, electromagnetic theory, and quantum mechanics will find this a useful textbook and reference work."--Jacket.

This book covers the fundamentals and significance of 2-D materials and related semiconductor transistor technologies for the next-generation ultra low power applications. It provides comprehensive coverage on advanced low power transistors such as NCFETs, FinFETs, TFETs, and flexible transistors for future ultra low power applications owing to their better subthreshold swing and scalability. In addition, the text examines the use of field-effect transistors for biosensing applications and covers design considerations and compact modeling of advanced low power transistors such as NCFETs, FinFETs, and TFETs. TCAD simulation examples are also provided. FEATURES Discusses the latest updates in the field of ultra low power semiconductor transistors Provides both experimental and analytical solutions for TFETs and NCFETs Presents synthesis and fabrication processes for FinFETs Reviews details on 2-D materials and 2-D transistors Explores the application of FETs for biosensing in the healthcare field This book is aimed at researchers, professionals, and graduate students in electrical engineering, electronics and communication engineering, electron devices, nanoelectronics and nanotechnology, microelectronics, and solid-state circuits.

An introduction to the fundamentals of semiconductor physics and engineering This book discusses fundamental semiconductor physics of devices and on-chip interconnections for physicists and links these concepts to engineering applications and case studies of computer chips. The book is organized in three parts. The first part deals with the representation of information and computation. The second part covers semiconductor device physics within the context of computation. The third part reviews chip design and semiconductor fabrication. The

book includes relevant equations, with the aim of closing the gap in the existing literature with actual case studies and engineering applications. Examples are provided in each chapter to illustrate physical and electrical concepts through the use of high-performance silicon technologies. Introductory Semiconductor Device Physics for Chip Design and Manufacturing: Provides physical descriptions and illustrations with data visualizations to facilitate intuitive understanding of semiconductor physics, devices and on-chip interconnections Blends theoretical physics treatment with engineering applications and real case studies for manufactured chips Presents complementary-metal-oxide-semiconductor (CMOS) transistors in high-performance server microprocessors with static CMOS combinational digital circuit design examples Offers a rich array of student problem sets, mid-term exams, and final exams with a glossary at the end of the book M. Y. Lanzerotti, PhD, has over 15 years of engineering experience in designing integrated circuits for high-performance server chips and aerospace applications. Dr. Lanzerotti is Assistant Professor of Physics at Augsburg College and previously held positions as Associate Professor of Computer Engineering at Air Force Institute of Technology, Instructor at Harvard Summer School, Visiting Faculty Fellow at Pacific Lutheran University, Visiting Faculty Fellow at Sapienza University of Rome, and Research Staff Member at IBM Thomas J. Watson Research Center. This book is inspired from Dr. Lanzerotti's course, "Introductory Semiconductor Device Physics for Chip Design and Manufacturing," at Harvard Summer School. Dr. Lanzerotti holds physics degrees from Harvard College, the University of Cambridge, and Cornell University. Dr. Lanzerotti holds four U.S. patents, was awarded an IEEE Technical Innovation Award in 2007 and an IBM Outstanding Research Contribution Award in 1998, and was Editor-in-Chief of the IEEE Solid-

State Circuits Society Magazine.

This book provides one of the most rigorous treatments of compound semiconductor device physics yet published. A complete understanding of modern devices requires a working knowledge of low-dimensional physics, the use of statistical methods, and the use of one-, two-, and three-dimensional analytical and numerical analysis techniques. With its systematic and detailed\*\*discussion of these topics, this book is ideal for both the researcher and the student. Although the emphasis of this text is on compound semiconductor devices, many of the principles discussed will also be useful to those interested in silicon devices. Each chapter ends with exercises that have been designed to reinforce concepts, to complement arguments or derivations, and to emphasize the nature of approximations by critically evaluating realistic conditions. One of the most rigorous treatments of compound semiconductor device physics yet published\*\*Essential reading for a complete understanding of modern devices\*\*Includes chapter-ending exercises to facilitate understanding

Semiconductor power devices are the heart of power electronics. They determine the performance of power converters and allow topologies with high efficiency.

Semiconductor properties, pn-junctions and the physical phenomena for understanding power devices are discussed in depth. Working principles of state-of-the-art power diodes, thyristors, MOSFETs and IGBTs are explained in detail, as well as key aspects of semiconductor device production technology. In practice, not only the semiconductor,

but also the thermal and mechanical properties of packaging and interconnection technologies are essential to predict device behavior in circuits. Wear and aging mechanisms are identified and reliability analyses principles are developed. Unique information on destructive mechanisms, including typical failure pictures, allows assessment of the ruggedness of power devices. Also parasitic effects, such as device induced electromagnetic interference problems, are addressed. The book concludes with modern power electronic system integration techniques and trends.

Semiconductors are at the heart of modern living. Almost everything we do, be it work, travel, communication, or entertainment, all depend on some feature of semiconductor technology. Comprehensive Semiconductor Science and Technology captures the breadth of this important field, and presents it in a single source to the large audience who study, make, and exploit semiconductors. Previous attempts at this achievement have been abbreviated, and have omitted important topics. Written and Edited by a truly international team of experts, this work delivers an objective yet cohesive global review of the semiconductor world. The work is divided into three sections. The first section is concerned with the fundamental physics of semiconductors, showing how the electronic features and the lattice dynamics change drastically when systems vary from bulk to a low-dimensional structure and further to a nanometer size. Throughout this section there is an emphasis on the full understanding of the underlying physics. The second section deals largely with the transformation of the conceptual framework of

solid state physics into devices and systems which require the growth of extremely high purity, nearly defect-free bulk and epitaxial materials. The last section is devoted to exploitation of the knowledge described in the previous sections to highlight the spectrum of devices we see all around us. Provides a comprehensive global picture of the semiconductor world Each of the work's three sections presents a complete description of one aspect of the whole Written and Edited by a truly international team of experts

Electrical Engineering Advanced Theory of Semiconductor Devices Semiconductor devices are ubiquitous in today's world and are found increasingly in cars, kitchens and electronic door locks, attesting to their presence in our daily lives. This comprehensive book provides the fundamentals of semiconductor device theory from basic quantum physics to computer-aided design. Advanced Theory of Semiconductor Devices will improve your understanding of computer simulation of devices through a thorough discussion of basic equations, their validity, and numerical solutions as they are contained in current simulation tools. You will gain state-of-the-art knowledge of devices used in both III–V compounds and silicon technology. Specially featured are novel approaches and explanations of electronic transport, particularly in p–n junction diodes. Close attention is also given to innovative treatments of quantum-well laser diodes and hot electron effects in silicon technology. This in-depth book is written for engineers, graduate students, and research scientists in solid-state electronics who want to gain a

better understanding of the principles underlying semiconductor devices.

The purpose of this workshop is to spread the vast amount of information available on semiconductor physics to every possible field throughout the scientific community. As a result, the latest findings, research and discoveries can be quickly disseminated. This workshop provides all participating research groups with an excellent platform for interaction and collaboration with other members of their respective scientific community. This workshop's technical sessions include various current and significant topics for applications and scientific developments, including • Optoelectronics • VLSI & ULSI Technology • Photovoltaics • MEMS & Sensors • Device Modeling and Simulation • High Frequency/ Power Devices • Nanotechnology and Emerging Areas • Organic Electronics • Displays and Lighting Many eminent scientists from various national and international organizations are actively participating with their latest research works and also equally supporting this mega event by joining the various organizing committees.

Filling the gap in the literature currently available, this book presents an overview of our knowledge of the physics behind organic semiconductor devices. Contributions from 18 international research groups cover various aspects of this field, ranging from the growth of organic layers and crystals, their electronic properties at interfaces, their photophysics and electrical transport properties to the application of these materials in such different devices as organic field-effect transistors, photovoltaic cells and organic

light-emitting diodes. From the contents: \* Excitation Dynamics in Organic Semiconductors \* Organic Field-Effect Transistors \* Spectroscopy of Organic Semiconductors \* Interfaces between Organic Semiconductors and Metals \* Analysis and Modeling of Devices \* Exciton Formation and Energy Transfer in Organic Light Emitting Diodes \* Deposition and Characterization

SEMICONDUCTOR DEVICES: PHYSICS AND TECHNOLOGY, 2ND ED John Wiley & Sons

The 3rd edition of this successful textbook contains ample material for a comprehensive upper-level undergraduate or beginning graduate course, guiding readers to the point where they can choose a special topic and begin supervised research. The textbook provides a balance between essential aspects of solid-state and semiconductor physics, on the one hand, and the principles of various semiconductor devices and their applications in electronic and photonic devices, on the other. It highlights many practical aspects of semiconductors such as alloys, strain, heterostructures, nanostructures, that are necessary in modern semiconductor research but typically omitted in textbooks. Coverage also includes additional advanced topics, such as Bragg mirrors, resonators, polarized and magnetic semiconductors, nanowires, quantum dots, multi-junction solar cells, thin film transistors, carbon-based nanostructures and transparent conductive oxides. The text derives explicit formulas for many results to support better understanding of the topics. The Physics of Semiconductors requires little or no prior

knowledge of solid-state physics and evolved from a highly regarded two-semester course. In the third edition several topics are extended and treated in more depth including surfaces, disordered materials, amorphous semiconductors, polarons, thermopower and noise. More than 1800 references guide the reader to historic and current literature including original and review papers and books.

This book addresses material growth, device fabrication, device application, and commercialization of energy-efficient white light-emitting diodes (LEDs), laser diodes, and power electronics devices. It begins with an overview on basics of semiconductor materials, physics, growth and characterization techniques, followed by detailed discussion of advantages, drawbacks, design issues, processing, applications, and key challenges for state of the art GaN-based devices. It includes state of the art material synthesis techniques with an overview on growth technologies for emerging bulk or free standing GaN and AlN substrates and their applications in electronics, detection, sensing, optoelectronics and photonics. Wengang (Wayne) Bi is Distinguished Chair Professor and Associate Dean in the College of Information and Electrical Engineering at Hebei University of Technology in Tianjin, China. Hao-chung (Henry) Kuo is Distinguished Professor and Associate Director of the Photonics Center at National Chiao-Tung University, Hsin-Tsu, Taiwan, China. Pei-Cheng

Ku is an associate professor in the Department of Electrical Engineering & Computer Science at the University of Michigan, Ann Arbor, USA. Bo Shen is the Cheung Kong Professor at Peking University in China.

Halbleiter-Leistungsbaulemente sind das Kernstück der Leistungselektronik. Sie bestimmen die Leistungsfähigkeit und machen neuartige und verlustarme Schaltungen erst möglich. In dem Band wird neben den Halbleiter-Leistungsbaulementen selbst auch die Aufbau- und Verbindungstechnik behandelt: von den physikalischen Grundlagen und der Herstellungstechnologie über einzelne Bauelemente bis zu thermomechanischen Problemen, Zerstörungsmechanismen und Störungseffekten. Die 2., überarbeitete Auflage berücksichtigt technische Neuerungen und Entwicklungen.

Learn the basic properties and designs of modern VLSI devices, as well as the factors affecting performance, with this thoroughly updated second edition. The first edition has been widely adopted as a standard textbook in microelectronics in many major US universities and worldwide. The internationally renowned authors highlight the intricate interdependencies and subtle trade-offs between various practically important device parameters, and provide an in-depth discussion of device scaling and scaling limits of CMOS and bipolar devices. Equations and parameters provided are checked continuously against the reality

of silicon data, making the book equally useful in practical transistor design and in the classroom. Every chapter has been updated to include the latest developments, such as MOSFET scale length theory, high-field transport model and SiGe-base bipolar devices.

Computing and information and communications technology (ICT) has dramatically changed how we work and live, has had profound effects on nearly every sector of society, has transformed whole industries, and is a key component of U.S. global leadership. A fundamental driver of advances in computing and ICT has been the fact that the single-processor performance has, until recently, been steadily and dramatically increasing year over years, based on a combination of architectural techniques, semiconductor advances, and software improvements. Users, developers, and innovators were able to depend on those increases, translating that performance into numerous technological innovations and creating successive generations of ever more rich and diverse products, software services, and applications that had profound effects across all sectors of society. However, we can no longer depend on those extraordinary advances in single-processor performance continuing. This slowdown in the growth of single-processor computing performance has its roots in fundamental physics and engineering constraints--multiple technological barriers have

converged to pose deep research challenges, and the consequences of this shift are deep and profound for computing and for the sectors of the economy that depend on and assume, implicitly or explicitly, ever-increasing performance. From a technology standpoint, these challenges have led to heterogeneous multicore chips and a shift to alternate innovation axes that include, but are not limited to, improving chip performance, mobile devices, and cloud services. As these technical shifts reshape the computing industry, with global consequences, the United States must be prepared to exploit new opportunities and to deal with technical challenges. The New Global Ecosystem in Advanced Computing: Implications for U.S. Competitiveness and National Security outlines the technical challenges, describe the global research landscape, and explore implications for competition and national security.

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